

## General Description

The 8400110 is a Low Jitter Telecom Rate-Conversion PLL that provides accurate and reliable frequency conversion.

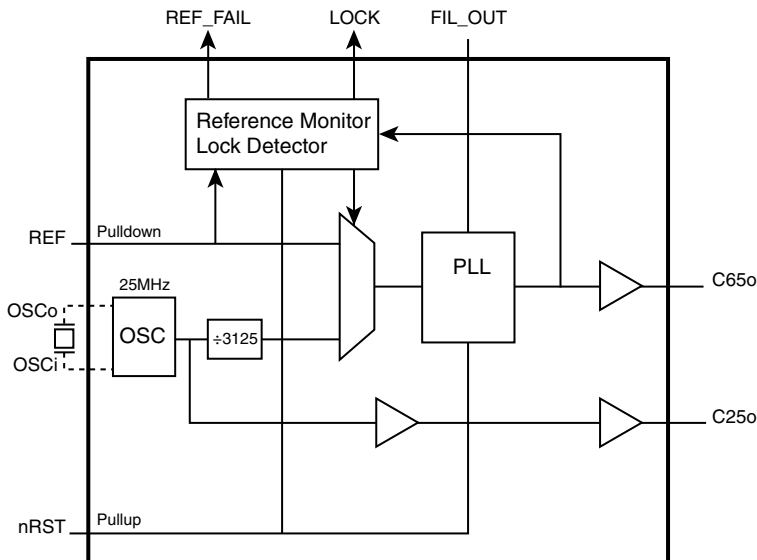
The 8400110 generates a 65.536MHz clock that is either locked to the input reference or locked to the external crystal or oscillator.

In the locked mode, the reference input is continuously monitored for a failure condition. In the event of a failure, the PLL continues to provide a stable free-running clock, ensuring system reliability.

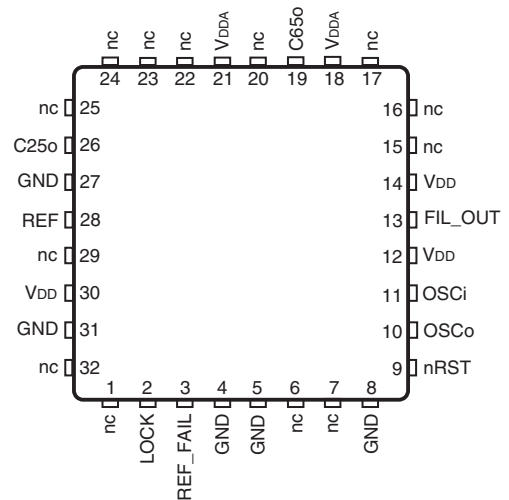
## Features

- One 65.536MHz output, synchronized to 8kHz reference
- One 25MHz output, buffered version of the internal osc output
- Provides lock and reference fail indication
- Free run mode when reference clock (REF) fails
- Automatic switch-over to reference when good reference (REF) is available
- 25MHz external master clock source: crystal or oscillator
- Full 3.3V operation
- -40°C to 85°C ambient operating temperature
- Available in a lead-free (RoHS 6) package

## Block Diagram



## Pin Assignment



**8400110**

**32-Lead VFQFN**

**5mm x 5mm x 0.925mm package body**

**K Package**

**Top View**

## Pin Description and Pin Characteristic Tables

**Table 1. Pin Descriptions**

| Number  | Name             | Type   |          | Description  |
|---|------------------|--------|----------|--|
| 1, 6, 7, 15, 16, 17, 20, 22, 23, 24, 25, 29, 32 | nc               | Unused |          | No connect.  |
| 2   | LOCK             | Output |          | Lock indicator. When HIGH, the PLL is frequency locked to a valid input reference. LVCMOS/LVTTL interface levels.  |
| 3   | REF_FAIL         | Output |          | Reference fail indicator. A logic HIGH at this output indicates that the reference (REF) frequency is exhibiting abrupt phase or frequency change. LVCMOS/LVTTL interface levels.  |
| 4, 5, 8, 27, 31                                 | GND              | Power  |          | Power supply ground.   |
| 9   | nRST             | Input  | Pullup   | Reset. A logic LOW at this input resets the device. In Reset state, all outputs are forced into high-impedance. LVCMOS/LVTTL interface levels.   |
| 10  | OSCo             | Output |          | Crystal out.   |
| 11  | OSCi             | Input  |          | Crystal in or single ended clock input.  |
| 12, 14, 30                                      | V <sub>DD</sub>  | Power  |          | Core supply pins.  |
| 13  | FIL_OUT          | Output |          | Filter output pin connected to 4.7μF capacitor.  |
| 18, 21  | V <sub>DDA</sub> | Power  |          | Analog supply pins.  |
| 19  | C65o             | Output |          | Single-ended clock output, 65.536MHz frequency. This output is used for general TDM applications. LVCMOS/LVTTL interface levels.   |
| 26  | C25o             | Output |          | Single-ended clock output, 25MHz frequency. This is a buffered version of internal crystal oscillator. The phase and frequency accuracy of this output tracks that of the external crystal or oscillator. LVCMOS/LVTTL interface levels. |
| 28  | REF              | Input  | Pulldown | This is the input reference source used for synchronization. LVCMOS/LVTTL interface levels.  |

NOTE: Pullup and Pulldown refer to internal input resistors. See Table 2, *Pin Characteristics*, for typical values.

**Table 2. Pin Characteristics**

| Symbol                | Parameter               | Test Conditions         | Minimum | Typical | Maximum | Units |
|-----------------------|-------------------------|-------------------------|---------|---------|---------|-------|
| C <sub>IN</sub>       | Input Capacitance       |                         |         | 4       |         | pF    |
| R <sub>PULLUP</sub>   | Input Pullup Resistor   |                         |         | 51      |         | kΩ    |
| R <sub>PULLDOWN</sub> | Input Pulldown Resistor |                         |         | 51      |         | kΩ    |
| R <sub>OUT</sub>      | Output Impedance        | V <sub>DDO</sub> = 3.6V |         | 17      |         | Ω     |

## Functional Description

The PLL of 8400110 consists of a phase detector, a loop filter and a Voltage Controlled Oscillator (VCO). In the normal mode of operation, the VCO provides an output clock signal that is frequency and phase locked to the input reference clock (REF). In free-run mode, VCO is locked to 25MHz input with an accuracy equal to the accuracy of the OSCi 25MHz clock.

### Lock Indicator

The Lock detector monitors if the output clock phase is within 90° of the input reference (REF). If the difference between input reference clock (REF) and output is more than 90°, LOCK output is LOW. The monitor then looks for eight consecutive clocks within 22.5° of the reference, before setting the LOCK to a HIGH.

### REF\_FAIL

The REF\_FAIL signal is HIGH when reference clock (REF) shows greater than 130ppm variation in frequency, there are more than three consecutive edges missing, or there is an abrupt phase shift in the reference clock REF. Under any of these circumstances the PLL input will be switched from primary reference clock (REF) to crystal. When the primary reference clock (REF) is restored and REF\_FAIL sets to LOW, the PLL input is switched back to the primary reference clock (REF).

### Modes of Operation

The 8400110 device has two modes of operation; normal mode and free-run mode. The device powers up in free-run mode, it automatically transitions to normal mode if a valid reference clock (REF) is available and transitions to free-run mode if the reference fails. RESET signal also will put the device in free-run mode.

### Freerun Mode

The freerun mode is typically used when an asynchronous clock source is required or it is used immediately following system power-up before synchronization is achieved. In free-run mode, 8400110 provides an output clock based on oscillator frequency. The output is not synchronized to the reference input clock (REF). In the free-run mode the accuracy of output frequency is equal to the accuracy of the frequency of the oscillator.

### Normal Mode

The normal mode is typically used when a synchronous clock is required. In normal mode, 8400110 provides an output clock which is synchronized to the input (REF).

### Lock Time

This is the time it takes the PLL to lock to the input reference clock REF. Lock occurs when the input signal and output signal are aligned in phase and frequency with respect to each other. LOCK time is affected by many factors which include:

- Initial input to output phase difference
- Initial input to output frequency difference
- PLL loop bandwidth

## Absolute Maximum Ratings

NOTE: Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These ratings are stress specifications only. Functional operation of product at these conditions or any conditions beyond those listed in the *DC Characteristics* or *AC Characteristics* is not implied. Exposure to absolute maximum rating conditions for extended periods may affect product reliability.

| Item                                     | Rating                   |
|--|--------------------------|
| Supply Voltage, $V_{DD}$                 | 4.6V                     |
| Inputs, $V_I$                            | -0.5V to $V_{DD} + 0.5V$ |
| Outputs, $V_O$                           | -0.5V to $V_{DD} + 0.5V$ |
| Package Thermal Impedance, $\theta_{JA}$ | 37°C/W                   |
| Storage Temperature, $T_{STG}$           | -65°C to 150°C           |

## DC Electrical Characteristics

**Table 3A. Power Supply DC Characteristics,  $V_{DD} = 3.3V \pm 0.3V$ ,  $T_A = -40^\circ C$  to  $85^\circ C$**

| Symbol    | Parameter             | Test Conditions          | Minimum          | Typical | Maximum  | Units |
|-----------|-----------------------|--------------------------|------------------|---------|----------|-------|
| $V_{DD}$  | Core Supply Voltage   |                          | 3.0              | 3.3     | 3.6      | V     |
| $V_{DDA}$ | Analog Supply Voltage |                          | $V_{DD} - 0.075$ | 3.3     | $V_{DD}$ | V     |
| $I_{DD}$  | Power Supply Current  | Output Frequency = 65MHz |                  |         | 130      | mA    |
| $I_{DDA}$ | Analog Supply Current | Output Frequency = 65MHz |                  |         | 15       | mA    |

**Table 3B. LVCMOS DC Characteristics,  $V_{DD} = 3.3V \pm 0.3V$ ,  $T_A = -40^\circ C$  to  $85^\circ C$**

| Symbol   | Parameter           | Test Conditions            | Minimum                         | Typical | Maximum        | Units   |
|----------|---------------------|----------------------------|---------------------------------|---------|----------------|---------|
| $V_{IH}$ | Input High Voltage  |                            | 2                               |         | $V_{DD} + 0.3$ | V       |
| $V_{IL}$ | Input Low Voltage   |                            | -0.3                            |         | 0.8            | V       |
| $I_{IH}$ | Input Current High  | REF                        | $V_{DD} = V_{IN} = 3.6V$        |         | 150            | $\mu A$ |
|          |                     | nRST                       | $V_{DD} = V_{IN} = 3.6V$        |         | 5              | $\mu A$ |
| $I_{IL}$ | Input Current Low   | REF                        | $V_{DD} = 3.6V, V_{IN} = 0V$    | -5      |                | $\mu A$ |
|          |                     | nRST                       | $V_{DD} = 3.6V, V_{IN} = 0V$    | -150    |                | $\mu A$ |
| $V_{OH}$ | Output High Voltage | C65o, C25o, REF_FAIL, LOCK | $V_{DD} = 3.6V, I_{OH} = -12mA$ | 2.6     |                | V       |
| $V_{OL}$ | Output Low Voltage  | C65o, C25o, REF_FAIL, LOCK | $V_{DD} = 3.6V, I_{OL} = 12mA$  |         | 0.5            | V       |

**Table 4. Crystal Characteristics**

| Parameter                          | Test Conditions | Minimum     | Typical | Maximum | Units    |
|------------------------------------|-----------------|-------------|---------|---------|----------|
| Mode of Oscillation                |                 | Fundamental |         |         |          |
| Frequency                          |                 |             | 25      |         | MHz      |
| Equivalent Series Resistance (ESR) |                 |             |         | 50      | $\Omega$ |
| Shunt Capacitance                  |                 |             |         | 7       | pF       |

## AC Electrical Characteristics

**Table 5. AC Characteristics,  $V_{DD} = 3.3V \pm 0.3V$ ,  $T_A = -40^{\circ}C$  to  $85^{\circ}C$**

| Symbol     | Parameter                         | Test Conditions                          | Minimum | Typical | Maximum | Units |
|------------|-----------------------------------|--|---------|---------|---------|-------|
| $t_{REFW}$ | Reference Pulse Width High or Low | $f = 8kHz$                               | 15      |         |         | ns    |
| $t_{C65L}$ | C65o Pulse Width Low              | $f = 65.536MHz$                          | 7.0     |         | 8       | ns    |
| $t_{ORF}$  | Output Clock Rise or Fall Time    | Rise/Fall Time,<br>20% to 80%, 15pF Load | 1.05    |         | 2.1     | ns    |
| $t_{C25L}$ | C25o Pulse Width Low              |  | 19      |         | 21      | ns    |

NOTE: Electrical parameters are guaranteed over the specified ambient operating temperature range, which is established when the device is mounted in a test socket with maintained transverse airflow greater than 500 lfm. The device will meet specifications after thermal equilibrium has been reached under these conditions.

## Performance Characteristics

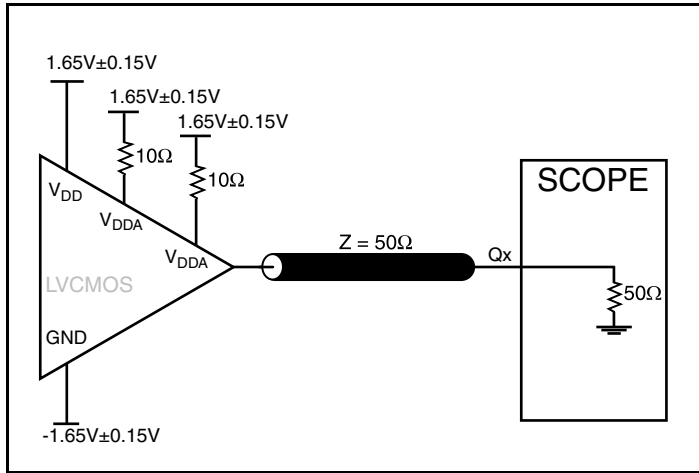
**Table 6. Functional Performance Characteristics**

| Characteristics                        | Test Conditions                    | Minimum | Typical | Maximum | Units |
|--|------------------------------------|---------|---------|---------|-------|
| PLL Capture Range                      |                                    | -150    |         | 150     | ppm   |
| PLL Lock Time                          | REF = 8kHz                         |         |         | 1       | s     |
| C65o Cycle-to-Cycle Jitter             | C65o = 65.536MHz                   |         |         | 100     | ps    |
| Peak-to-Peak Jitter C65.536;<br>NOTE 1 | C65o = 65.536MHz                   |         |         | 175     | ps    |
| RMS Phase Jitter C25o                  | 25MHz Crystal Input, 12kHz to 5MHz |         | 1       |         | ps    |

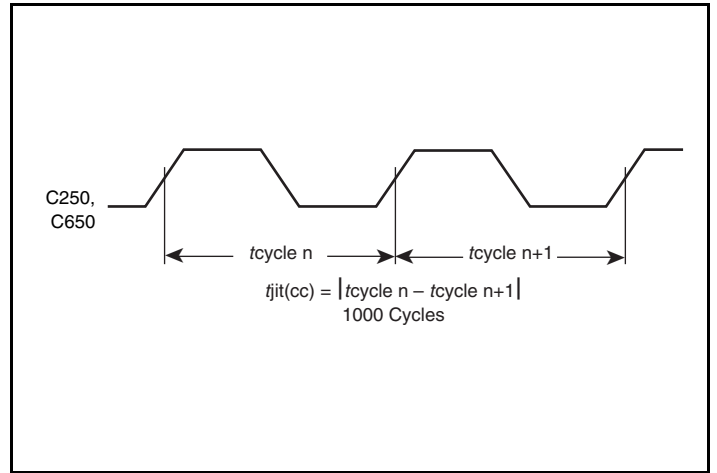
NOTE: Electrical parameters are guaranteed over the specified ambient operating temperature range, which is established when the device is mounted in a test socket with maintained transverse airflow greater than 500 lfm. The device will meet specifications after thermal equilibrium has been reached under these conditions.

NOTE 1: Peak-to-Peak jitter was calculated with RMS Period jitter data multiplied by BER 14.

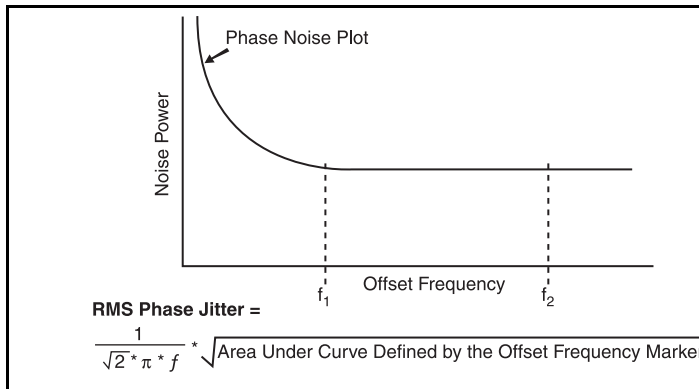
## Parameter Measurement Information



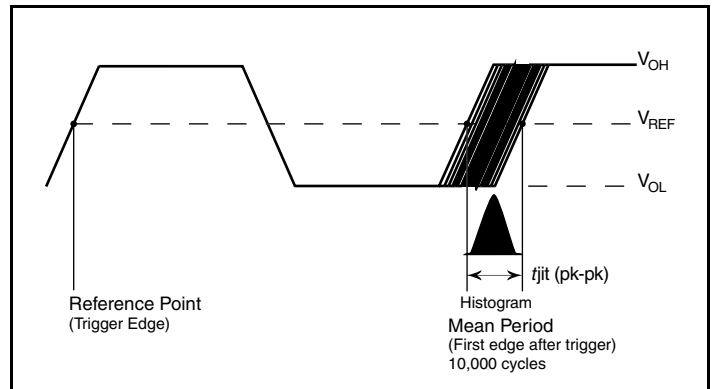
Output Load AC Test Circuit



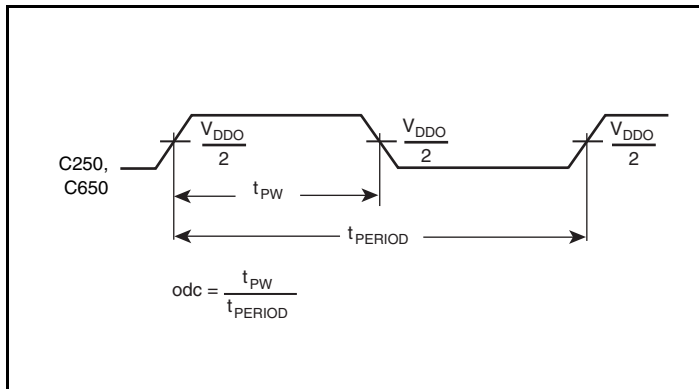
Cycle-to-Cycle Jitter



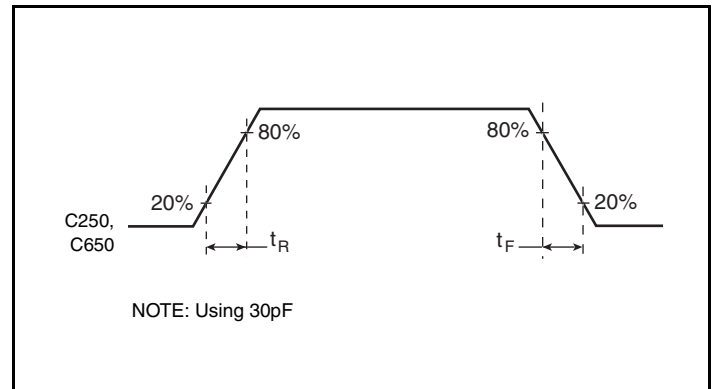
RMS Phase Jitter



Period Jitter Peak-to-Peak

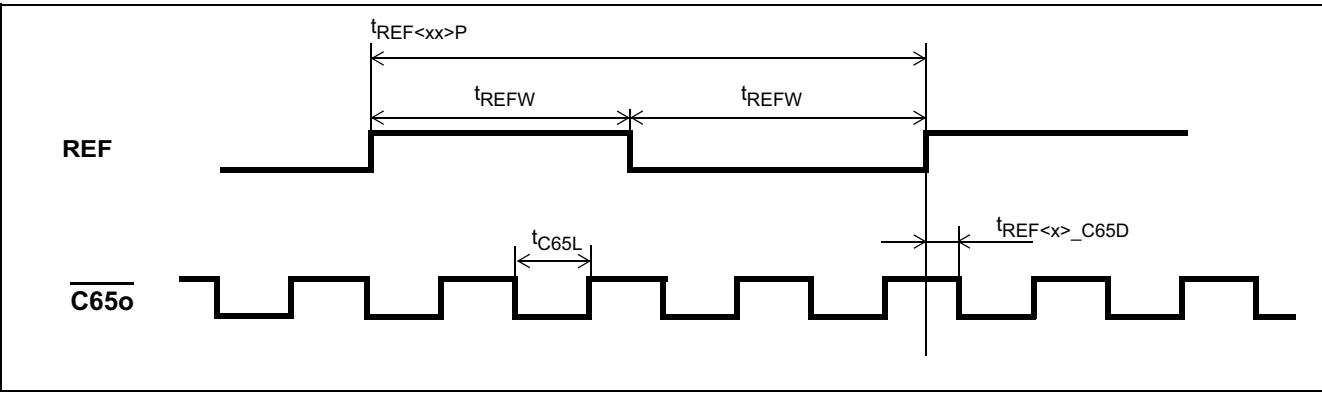


Output Pulse Width



Output Rise/Fall Time

## Parameter Measurement Information, continued



### Input-to-Output Timing for Synchronous Clock

## Application Information

### Power Supply Filtering Technique

As in any high speed analog circuitry, the power supply pins are vulnerable to random noise. To achieve optimum jitter performance, power supply isolation is required. The 8400110 provides separate power supplies to isolate any high switching noise from the outputs to the internal PLL.  $V_{DD}$  and  $V_{DDA}$  should be individually connected to the power supply plane through vias, and  $0.01\mu\text{F}$  bypass capacitors should be used for each pin. *Figure 1* illustrates this for a generic  $V_{DD}$  pin and also shows that  $V_{DDA}$  requires that an additional  $10\Omega$  resistor along with a  $10\mu\text{F}$  bypass capacitor be connected to the  $V_{DDA}$  pin.

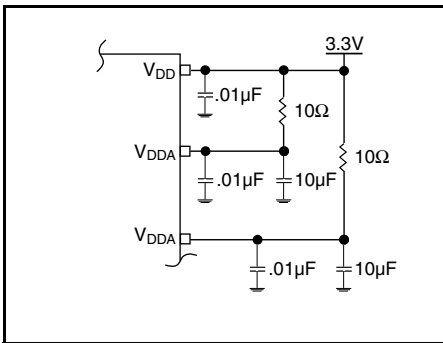
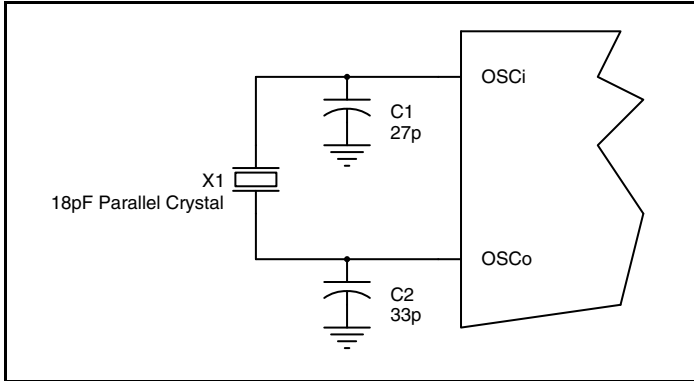


Figure 1. Power Supply Filtering

## Crystal Input Interface

The 8400110 has been characterized with 18pF parallel resonant crystals. The capacitor values, C1 and C2, shown in *Figure 2* below were determined using a 25MHz, 18pF parallel resonant crystal and

were chosen to minimize the ppm error. The optimum C1 and C2 values can be slightly adjusted for different board layouts.

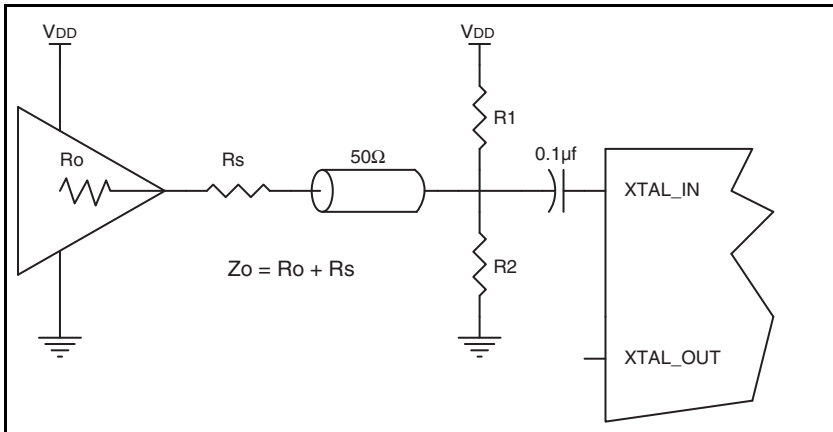


**Figure 2. Crystal Input Interface**

## LVC MOS to XTAL Interface

The OSCi input can accept a single-ended LVC MOS signal through an AC coupling capacitor. A general interface diagram is shown in *Figure 3*. The OSCo pin can be left floating. The input edge rate can be as slow as 10ns. For LVC MOS signals, it is recommended that the amplitude be reduced from full swing to half swing in order to prevent signal interference with the power rail and to reduce noise. This configuration requires that the output impedance of the driver ( $R_o$ ) plus the series resistance ( $R_s$ ) equals the transmission line

impedance. In addition, matched termination at the crystal input will attenuate the signal in half. This can be done in one of two ways. First,  $R_1$  and  $R_2$  in parallel should equal the transmission line impedance. For most 50Ω applications,  $R_1$  and  $R_2$  can be 100Ω. This can also be accomplished by removing  $R_1$  and making  $R_2$  50Ω. By overdriving the crystal oscillator, the device will be functional, but note, the device performance is guaranteed by using a quartz crystal.



**Figure 3. General Diagram for LVC MOS Driver to XTAL Input Interface**

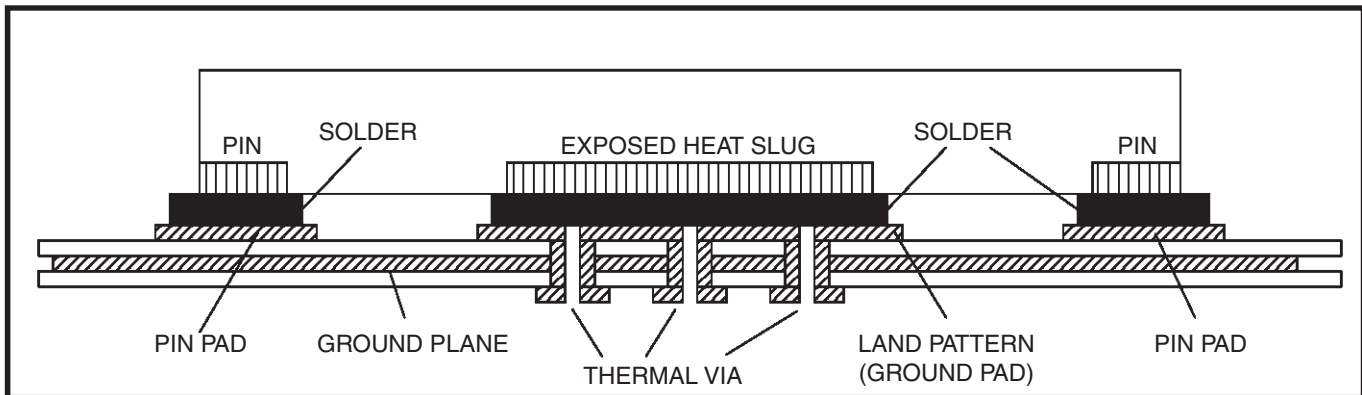


## VFQFN EPAD Thermal Release Path

In order to maximize both the removal of heat from the package and the electrical performance, a land pattern must be incorporated on the Printed Circuit Board (PCB) within the footprint of the package corresponding to the exposed metal pad or exposed heat slug on the package, as shown in *Figure 4*. The solderable area on the PCB, as defined by the solder mask, should be at least the same size/shape as the exposed pad/slug area on the package to maximize the thermal/electrical performance. Sufficient clearance should be designed on the PCB between the outer edges of the land pattern and the inner edges of pad pattern for the leads to avoid any shorts.

While the land pattern on the PCB provides a means of heat transfer and electrical grounding from the package to the board through a solder joint, thermal vias are necessary to effectively conduct from the surface of the PCB to the ground plane(s). The land pattern must be connected to ground through these vias. The vias act as “heat pipes”. The number of vias (i.e. “heat pipes”) are application specific

and dependent upon the package power dissipation as well as electrical conductivity requirements. Thus, thermal and electrical analysis and/or testing are recommended to determine the minimum number needed. Maximum thermal and electrical performance is achieved when an array of vias is incorporated in the land pattern. It is recommended to use as many vias connected to ground as possible. It is also recommended that the via diameter should be 12 to 13mils (0.30 to 0.33mm) with 1oz copper via barrel plating. This is desirable to avoid any solder wicking inside the via during the soldering process which may result in voids in solder between the exposed pad/slug and the thermal land. Precautions should be taken to eliminate any solder voids between the exposed heat slug and the land pattern. Note: These recommendations are to be used as a guideline only. For further information, please refer to the Application Note on the Surface Mount Assembly of Amkor's Thermally/Electrically Enhance Leadframe Base Package, Amkor Technology.



**Figure 4. P.C. Assembly for Exposed Pad Thermal Release Path – Side View (drawing not to scale)**

## Power Considerations

This section provides information on power dissipation and junction temperature for the 8400110. Equations and example calculations are also provided.

### 1. Power Dissipation.

The total power dissipation for the 8400110 is the sum of the core power plus the analog power plus the power dissipation in the load(s). The following is the power dissipation for  $V_{DD} = 3.3V + 0.3V = 3.6V$ , which gives worst case results.

- Power (core)<sub>MAX</sub> =  $V_{DD\_MAX} * (I_{DD} + I_{DDA}) = 3.6V * (130mA + 15mA) = \mathbf{522mW}$
- Output Impedance  $R_{OUT}$  Power Dissipation due to Loading  $50\Omega$  to  $V_{DD}/2$   
Output Current  $I_{OUT} = V_{DD\_MAX} / [2 * (50\Omega + R_{OUT})] = 3.6V / [2 * (50\Omega + 17\Omega)] = \mathbf{26.9mA}$
- Power Dissipation on the  $R_{OUT}$  per LVCMOS output  
Power ( $R_{OUT}$ ) =  $R_{OUT} * (I_{OUT})^2 = 17\Omega * (26.9mA)^2 = \mathbf{12.3mW}$  per output
- Total Power Dissipation on the  $R_{OUT}$   
**Total Power ( $R_{OUT}$ ) =  $12.3mW * 2 = \mathbf{24.6mW}$**

### Total Power Dissipation

- Total Power**  
= Power (core)<sub>MAX</sub> + Total Power ( $R_{OUT}$ )  
=  $522mW + 24.6mW$   
= **546.6mW**

### 2. Junction Temperature.

Junction temperature,  $T_j$ , is the temperature at the junction of the bond wire and bond pad, and directly affects the reliability of the device. The maximum recommended junction temperature for devices is  $125^\circ\text{C}$ . Limiting the internal transistor junction temperature,  $T_j$ , to  $125^\circ\text{C}$  ensures that the bond wire and bond pad temperature remains below  $125^\circ\text{C}$ .

The equation for  $T_j$  is as follows:  $T_j = \theta_{JA} * Pd\_total + T_A$

$T_j$  = Junction Temperature

$\theta_{JA}$  = Junction-to-Ambient Thermal Resistance

$Pd\_total$  = Total Device Power Dissipation (example calculation is in section 1 above)

$T_A$  = Ambient Temperature

In order to calculate junction temperature, the appropriate junction-to-ambient thermal resistance  $\theta_{JA}$  must be used. Assuming no air flow and a multi-layer board, the appropriate value is  $37^\circ\text{C/W}$  per Table 7 below.

Therefore,  $T_j$  for an ambient temperature of  $85^\circ\text{C}$  with all outputs switching is:

$$85^\circ\text{C} + 0.547W * 37^\circ\text{C/W} = 105.2^\circ\text{C}. \text{ This is below the limit of } 125^\circ\text{C}.$$

This calculation is only an example.  $T_j$  will obviously vary depending on the number of loaded outputs, supply voltage, air flow and the type of board (multi-layer).

**Table 7. Thermal Resistance  $\theta_{JA}$  for 32 Lead VFQFN, Forced Convection**

| $\theta_{JA}$ by Velocity                   |                        |                        |                        |
|---|------------------------|------------------------|------------------------|
| Meters per Second                           | 0                      | 1                      | 2.5                    |
| Multi-Layer PCB, JEDEC Standard Test Boards | $37.0^\circ\text{C/W}$ | $32.4^\circ\text{C/W}$ | $29.0^\circ\text{C/W}$ |

## Reliability Information

**Table 8.  $\theta_{JA}$  vs. Air Flow Table for a 32 Lead VFQFN**

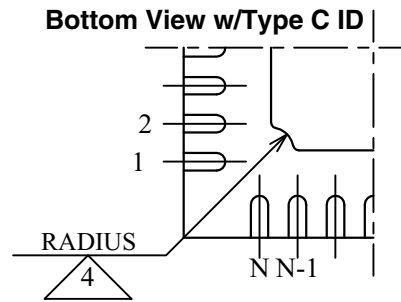
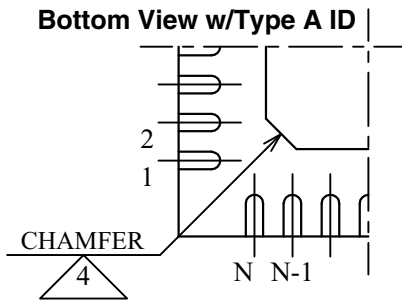
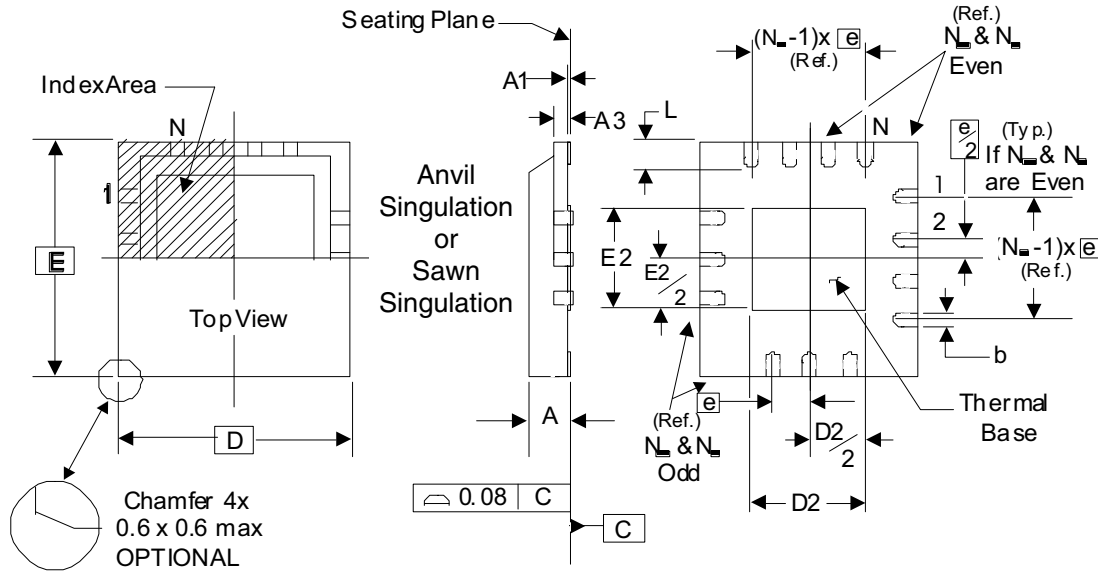
| $\theta_{JA}$ by Velocity                   |          |          |          |
|---|----------|----------|----------|
| Meters per Second                           | 0        | 1        | 2.5      |
| Multi-Layer PCB, JEDEC Standard Test Boards | 37.0°C/W | 32.4°C/W | 29.0°C/W |

## Transistor Count

The transistor count for 8400110 is: 4007

# Package Outline and Package Dimensions

## Package Outline - K Suffix for 32 Lead VFQFN



There are 2 methods of indicating pin 1 corner at the back of the VFQFN package:

1. Type A: Chamfer on the paddle (near pin 1)
2. Type C: Mouse bite on the paddle (near pin 1)

**Table 9. Package Dimensions for 32 Lead VFQFN**

| JEDEC Variation: VHHD-2/-4<br>All Dimensions in Millimeters |            |         |         |
|---|------------|---------|---------|
| Symbol  | Minimum    | Nominal | Maximum |
| N   | 32         |         |         |
| A   | 0.80       |         | 1.00    |
| A1  | 0          |         | 0.05    |
| A3  | 0.25 Ref.  |         |         |
| b   | 0.18       | 0.25    | 0.30    |
| $N_D$ & $N_E$   |            |         | 8       |
| D & E   | 5.00 Basic |         |         |
| D2 & E2   | 3.0        |         | 3.3     |
| e   | 0.50 Basic |         |         |
| L   | 0.30       | 0.40    | 0.50    |

Reference Document: JEDEC Publication 95, MO-220

**NOTE:** The following package mechanical drawing is a generic drawing that applies to any pin count VFQFN package. This drawing is not intended to convey the actual pin count or pin layout of this device. The pin count and pinout are shown on the front page. The package dimensions are in Table 9.

## Ordering Information

Table 10. Ordering Information

| Part/Order Number | Marking     | Package                   | Shipping Packaging | Temperature   |
|-------------------|-------------|---------------------------|--------------------|---------------|
| 8400110EKILF      | ICS00110EIL | "Lead-Free" 32 Lead VFQFN | Tray               | -40°C to 85°C |
| 8400110EKILFT     | ICS00110EIL | "Lead-Free" 32 Lead VFQFN | Tape & Reel        | -40°C to 85°C |

## Revision History Sheet

| Rev | Table | Page    | Description of Change  | Date    |
|-----|-------|---------|--|---------|
| B   | T10   | 1<br>13 | <p>"General Description" - deleted <i>HiperClocks</i> logo.</p> <p>Ordering Information Table - deleted <i>Tape &amp; Reel count</i>.</p> <p>Deleted all <i>HiperClocks</i> references throughout the datasheet.</p> <p>Deleted <i>ICS</i> prefix from part number throughout the datasheet.</p> <p>Updated datasheet header/footer.</p> | 1/20/16 |



## Notice

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